

Molding Type Module IGBT, 2 in 1 Package, 1200 V, 75 A


INT-A-PAK
FEATURES

- High short circuit capability, self limiting to $6 \times I_C$
- 10 μ s short circuit capability
- $V_{CE(on)}$ with positive temperature coefficient
- Rugged with ultrafast performance
- Square RBSOA
- Low inductance case
- Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**
PRODUCT SUMMARY

V_{CES}	1200 V
I_C at $T_C = 80^\circ\text{C}$	75 A
$V_{CE(on)}$ (typical) at $I_C = 75\text{ A}, 25^\circ\text{C}$	3.2 V
Speed	8 kHz to 30 kHz
Package	INT-A-PAK
Circuit	Half bridge

TYPICAL APPLICATIONS

- Switching mode power supplies
- Inductive heating
- UPS
- Electronic welders

DESCRIPTION

Vishay's IGBT power module provides ultra low conduction loss as well as short circuit ruggedness. It is designed for applications such as general inverters and UPS.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Gate to emitter voltage	V_{GES}		± 20	
Collector current	I_C	$T_C = 25^\circ\text{C}$	105	A
		$T_C = 80^\circ\text{C}$	75	
Pulsed collector current	$I_{CM}^{(1)}$	$t_p = 1\text{ ms}$	150	
Diode continuous forward current	I_F		75	
Diode maximum forward current	I_{FM}		150	
Maximum power dissipation	P_D	$T_J = 150^\circ\text{C}$	500	
Short circuit withstand time	t_{SC}	$T_J = 125^\circ\text{C}$	10	μ s
RMS isolation voltage	V_{ISOL}	$f = 50\text{ Hz}, t = 1\text{ min}$	2500	V
I^2t -value, diode	I^2t	$V_R = 0\text{ V}, t = 10\text{ ms}, T_J = 125^\circ\text{C}$	1170	A^2s

Note

⁽¹⁾ Repetitive rating: pulse width limited by maximum junction temperature.



IGBT ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V _{(BR)CES}	T _J = 25 °C	1200	-	-	V
Collector to emitter voltage	V _{CE(on)}	V _{GE} = 15 V, I _C = 75 A, T _J = 25 °C	-	3.2	-	
		V _{GE} = 15 V, I _C = 75 A, T _J = 125 °C	-	3.7	-	
Gate to emitter threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 3 mA, T _J = 25 °C	4.5	5.1	5.5	
Collector cut-off current	I _{CES}	V _{CE} = V _{CES} , V _{GE} = 0 V, T _J = 25 °C	-	-	2.0	mA
Gate to emitter leakage current	I _{GES}	V _{GE} = V _{GES} , V _{CE} = 0 V, T _J = 25 °C	-	-	400	nA

SWITCHING CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on delay time	t _{d(on)}	V _{CC} = 600 V, I _C = 75 A, R _g = 15 Ω, V _{GE} = ± 15 V, T _J = 25 °C	-	160	-	ns
Rise time	t _r		-	80	-	
Turn-off delay time	t _{d(off)}		-	420	-	
Fall time	t _f		-	110	-	
Turn-on switching loss	E _{on}		V _{CC} = 600 V, I _C = 75 A, R _g = 15 Ω, V _{GE} = ± 15 V, T _J = 125 °C	-	5.7	-
Turn-off switching loss	E _{off}	-		1.9	-	
Turn-on delay time	t _{d(on)}	-		140	-	ns
Rise time	t _r	-		90	-	
Turn-off delay time	t _{d(off)}	-		460	-	
Fall time	t _f	-	150	-		
Turn-on switching loss	E _{on}	V _{GE} = 0 V, V _{CE} = 30 V, f = 1.0 MHz, T _J = 25 °C	-	6.8	-	mJ
Turn-off switching loss	E _{off}		-	3.2	-	
Input capacitance	C _{ies}		-	4.3	-	nF
Output capacitance	C _{oes}		-	0.40	-	
Reverse transfer capacitance	C _{res}		-	0.16	-	
SC data	I _{SC}	t _{sc} ≤ 10 μs, V _{GE} = 15 V, T _J = 125 °C, V _{CC} = 900 V, V _{CEM} ≤ 1200 V	-	235	-	A
Stray inductance	L _{CE}		-	-	30	nH
Module lead resistance, terminal to chip	R _{CC'+EE'}	T _C = 25 °C	-	0.75	-	mΩ

DIODE ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Diode forward voltage	V _F	I _F = 75 A	T _J = 25 °C	-	1.9	2.3	V
			T _J = 125 °C	-	2.0	2.4	
Diode reverse recovery charge	Q _{rr}	I _F = 75 A, V _R = 600 V, di/dt = -2000 A/μs, V _{GE} = -15 V	T _J = 25 °C	-	100	-	μC
			T _J = 125 °C	-	125	-	
Diode peak reverse recovery current	I _{rr}	I _F = 75 A, V _R = 600 V, di/dt = -2000 A/μs, V _{GE} = -15 V	T _J = 25 °C	-	80	-	A
			T _J = 125 °C	-	100	-	
Diode reverse recovery energy	E _{rec}	I _F = 75 A, V _R = 600 V, di/dt = -2000 A/μs, V _{GE} = -15 V	T _J = 25 °C	-	3.0	-	mJ
			T _J = 125 °C	-	6.0	-	



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		-40	-	150	°C
Storage temperature range	T_{STG}		-40	-	125	
Junction to case	R_{thJC}	IGBT (per 1/2 module)	-	-	0.25	K/W
		Diode (per 1/2 module)	-	-	0.40	
Case to sink	R_{thCS}	Conductive grease applied	-	0.05	-	
Mounting torque		Power terminal screw: M5	2.5 to 5.0			Nm
		Mounting screw: M6	3.0 to 5.0			
Weight of module			160			g

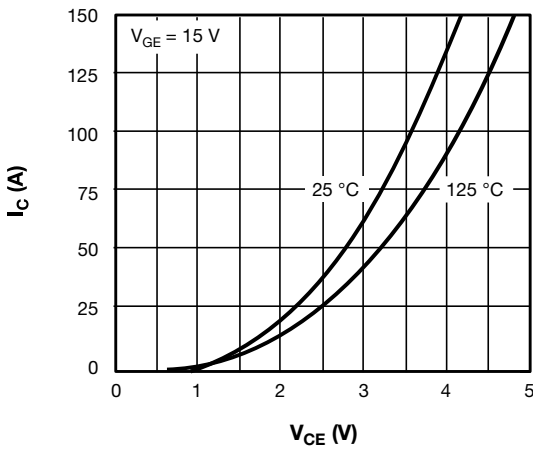


Fig. 1 - Typical Output Characteristics

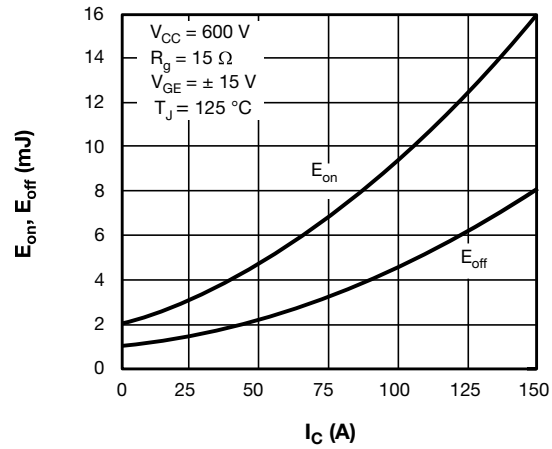


Fig. 3 - Total Switching Loss vs. I_C

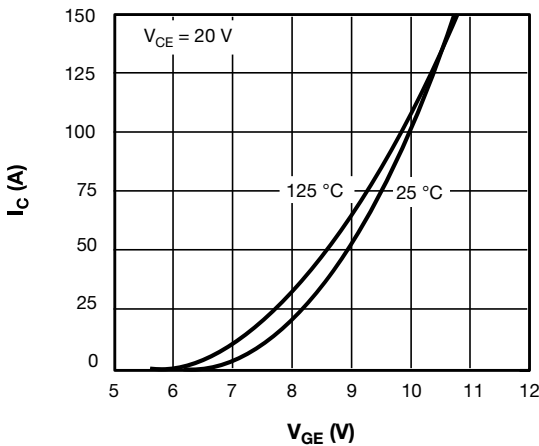


Fig. 2 - Typical Transfer Characteristics

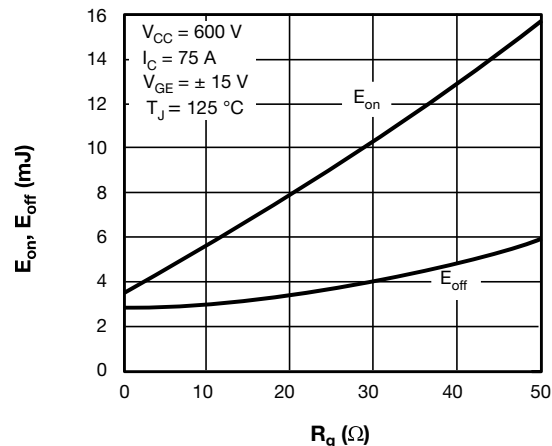


Fig. 4 - Total Switching Loss vs. R_g

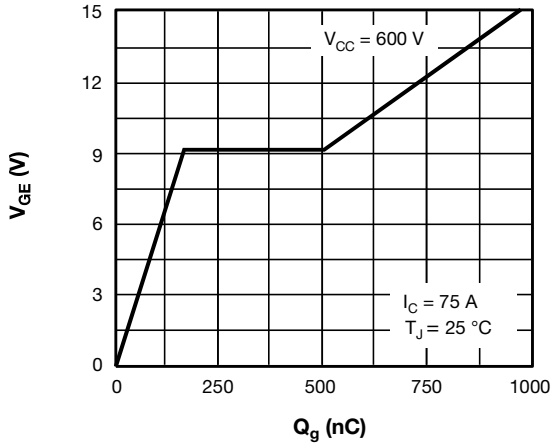


Fig. 5 - Gate Charge Characteristics

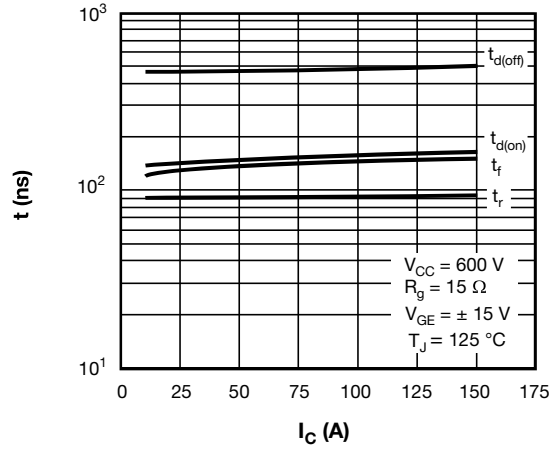


Fig. 7 - Typical Switching Times vs. I_C

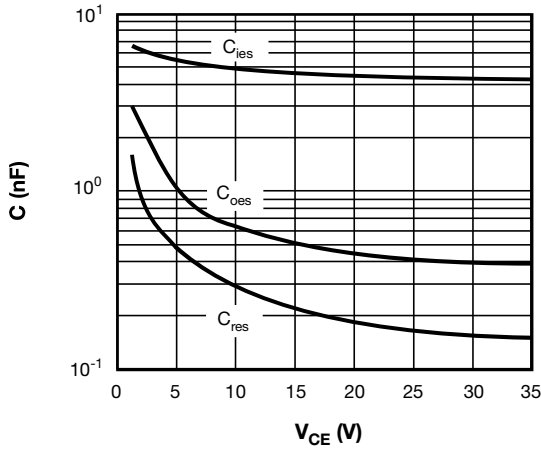


Fig. 6 - Typical Capacitance vs. Collector to Emitter Current

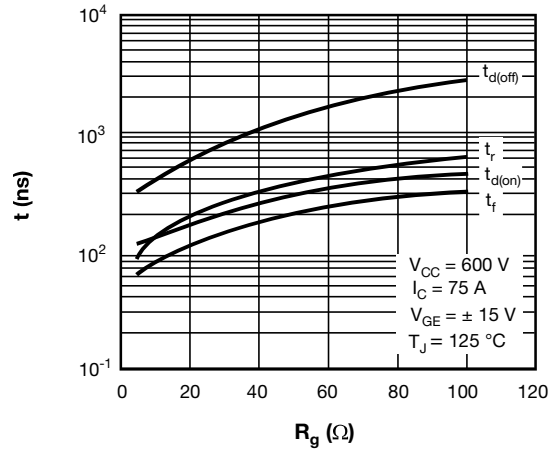


Fig. 8 - Typical Switching Times vs. Gate Resistance R_g

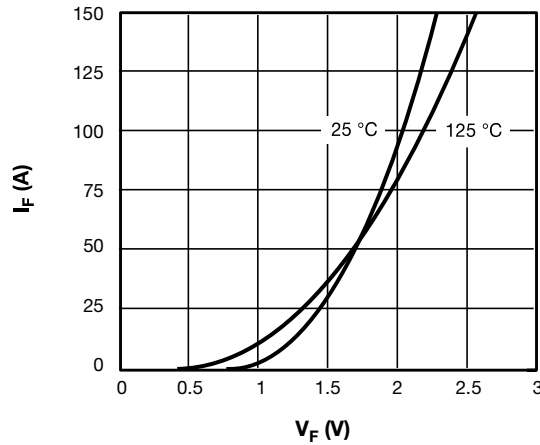


Fig. 9 - Diode Typical Forward Characteristics

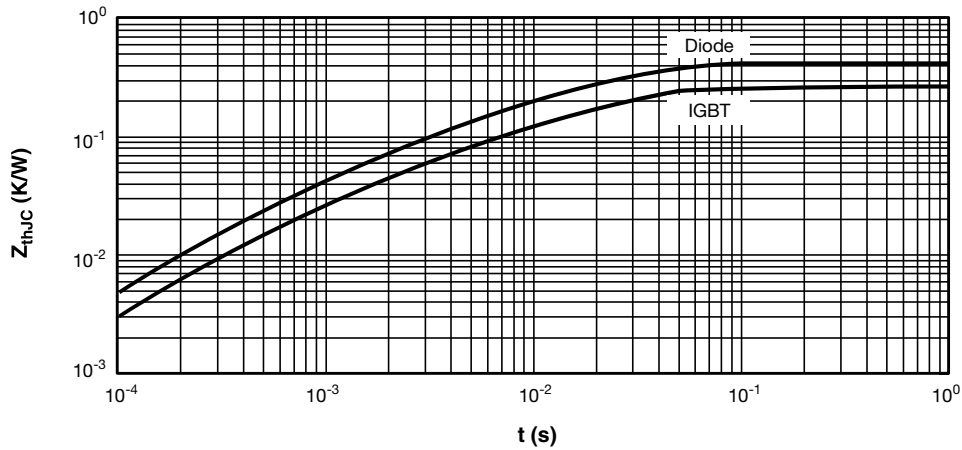
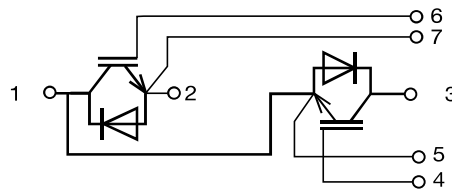


Fig. 10 - Transient Thermal Impedance

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95524



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